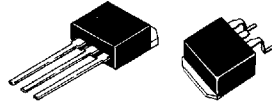


2SJ277



2093

2090

LD (Low Drive) Series $V_{DSS}=100V$

P Channel Power MOSFET

©4241

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Surface mount type device making the following possible.
 - Reduction in the number of manufacturing processes for 2SJ277-applied equipment.
 - High density surface mount applications.
 - Small size of 2SJ277-applied equipment.

Absolute Maximum Ratings at $T_a=25^\circ C$

			unit
Drain to Source Voltage	V_{DSS}	-100	V
Gate to Source Voltage	V_{GSS}	± 15	V
Drain Current(DC)	I_D	-15	A
Drain Current(Pulse)	I_{DP}	-60	A
Allowable Power Dissipation	P_D	1.65	W
	$T_c=25^\circ C$	70	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

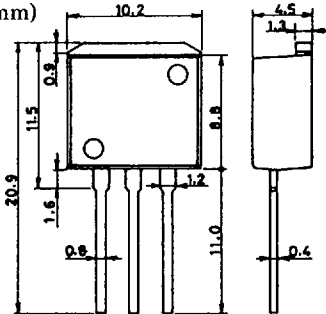
Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-100			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100V, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -8A$	7.5	13		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -8A, V_{GS} = -10V$		120	160	m Ω
	$R_{DS(on)}$	$I_D = -8A, V_{GS} = -4V$		160	220	m Ω

Continued on next page.

Package Dimensions 2093

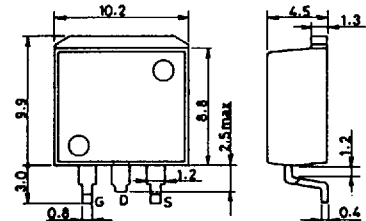
(unit : mm)



G : Gate
D : Drain
S : Source
SANYO : SMP

Package Dimensions 2090

(unit : mm)



G : Gate
D : Drain
S : Source
SANYO : SMP-FD

51193TH (KOTO) AX-8376 No.4241-1/3

Continued from preceding page.

			min	typ	max	unit
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		1900		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		400		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		80		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		18		ns
Rise Time	t_r	"		25		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		300		ns
Fall Time	t_f	"		120		ns
Diode Forward Voltage	V_{SD}	$I_S = -15A, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit

